Max. Marks: 70



Time: 3 Hours.

MARRI LAXMAN REDDY INSTITUTE OF TECHNOLOGY AND MANAGEMENT

(AN AUTONOMOUS INSTITUTION)
(Approved by AICTE, New Delhi & Affiliated to JNTUH, Hyderabad) Accredited by NBA and NAAC with 'A' Grade & Recognized Under Section2(f) & 12(B)of the UGC act, 1956

II B.Tech I Sem Supplementary Examination, July-2022 **Electronic Devices and Circuits** (ECE)

		ote: 1. Answer any FIVE questions. 2. Each question carries 14 marks and may have a, b as sub o	uestions		
1	a)	Explain the following terms (i) Static resistance (ii) Dynam resistance (iii) Junction resistance (iv) Reverse resistance of a Dioc with suitable figures.	ic 7M de	CO1	BL4
	b)	Draw the circuit diagram of Full-wave rectifier and derive the expressions for average value, R.M.S value and voltage drop acrodiode.	ne 7M ss	CO1	BL6
2	a)	A half wave rectifier has a load of 5.5 K Ω . If the diode resistance are the secondary coil resistance together have a resistance of 500 Ω are the input voltage has a signal voltage of 240 V, calculate i) Pea average and rms value of current flowing. ii) dc power output. iii) a power input iv) Efficiency of the rectifier.	ıd k,	CO1	BL3
	b)	Define diffusion and transition capacitance of p-n junction diod Prove that diffusion capacitance is proportional to current I.	e. 7M	CO1	BL3
3	a)	Sketch a family of CB input and output characteristics of for a transistor? Indicate the cutoff, active and saturation regions?	7M	CO2	BL3
	b)		it so	CO2	BL3
4	a)	List out different types of biasing methods. Derive the equation for stability factor for fixed bias.	or 7M	C02	BL6
	b)	Determine the quiescent currents and the collector to emitter voltage for a Ge transistor with β = 50 in the self biasing arrangements. The circuit component values are V_{CC} = 20V, R_{C} = 2k Ω , R_{e} = 0.1 k Ω , R_{1} = 100 k Ω and R_{2} = 5 k Ω . Find the stability factor S.		CO2	BL3
5	2)	Evaluin the working of Zoner diods as weltage regulator	773.4	CO2	D1.4
J	a) b)	Explain the working of Zener diode as voltage regulator. Discuss the characteristics and applications of UJT.	7M 7M	CO3	BL4 BL2
	2)	2.00 and office and applications of off.	/ 141	603	DLZ

6	a)	Explain the construction and operation of JFET and draw its characteristics.	7M	CO3	BL4
	b)	Explain how a FET is used as a voltage variable resistor.	7M	C03	BL4
7		Draw the circuit diagram of CC amplifier using hybrid parameters and derive the expression for $A_{\rm I}$, A_{V},R_{i} and $R_{0}.$	14M	CO4	BL
8		Explain the working of a n-channel depletion MOSFET. Discuss its characteristics.	14M	CO5	BL

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